

Abstract of the Disclosure

A TFT fabricated from a single crystal grain, and fabrication method has been provided. A large crystal grain is made by precise control of annealment, transition metal concentration, the density of transition metal nucleation sites, and the distance between nucleation sites. In one aspect of the invention, a diffusion layer permits the continual delivery of transition metal at a rate that both supports the lateral growth of di-silicide, and large distances between nucleation sites.

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